

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP504A, TLP504A-2

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

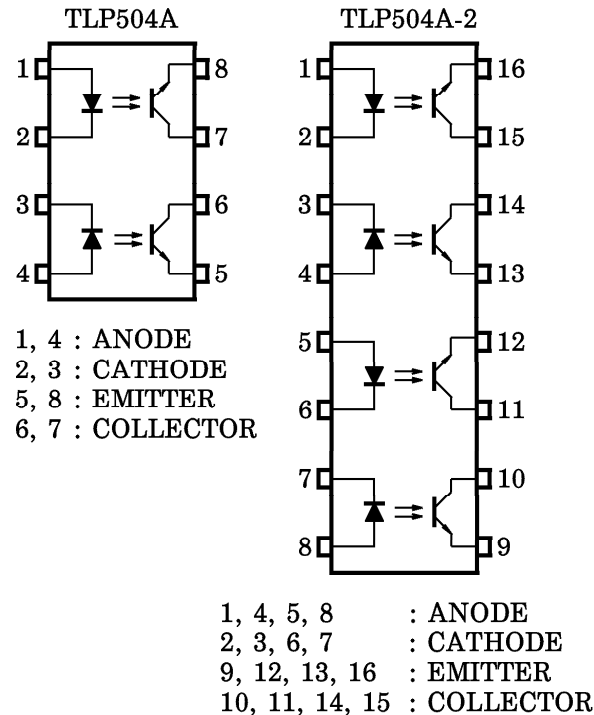
SOLID STATE RELAY

The TOSHIBA TLP504A and TLP504A-2 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode.

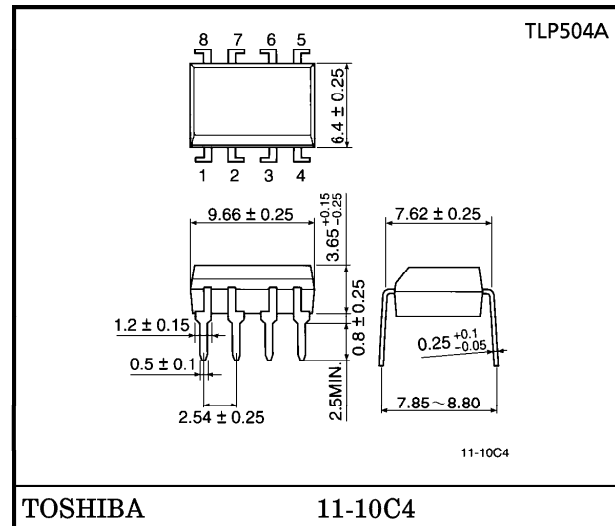
The TLP504A offers two isolated channels in a eight lead plastic DIP package, while the TLP504A-2 provides four isolated channels in a sixteen plastic DIP package.

- Collector-Emitter Voltage : 55V (Min.)
- Current Transfer Ratio : 50% (Min.)
Rank GB : 100% (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577,
File No. E67349

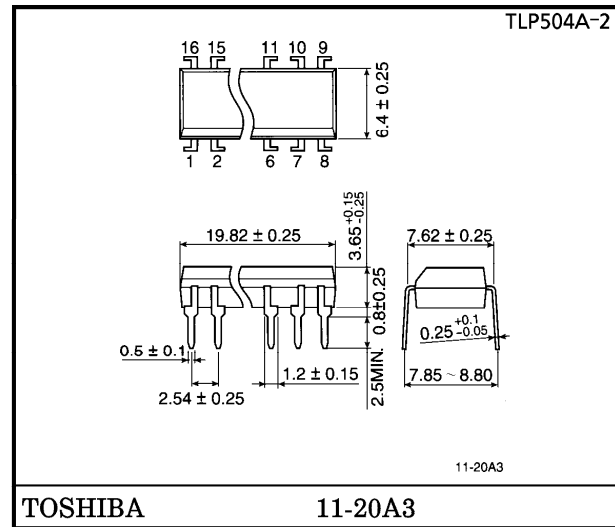
PIN CONFIGURATIONS (TOP VIEW)



Unit in mm



Weight : 0.54g



Weight : 1.1g

961001EBC2

● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING		UNIT
			TLP504A	TLP504A-2	
LED	Forward Current	I_F	60	50	mA
	Forward Current Derating	$\Delta I_F / ^\circ C$	-0.7 (Ta \geq 39°C)	-0.5 (Ta \geq 25°C)	mA / °C
	Pulse Forward Current	I_{FP}	1 (100 μ s pulse, 100pps)		A
	Reverse Voltage	V_R	5		V
	Junction Temperature	T_j	125		°C
DETECTOR	Collector-Emitter Voltage	V_{CEO}	55		V
	Emitter-Collector Voltage	V_{ECO}	7		V
	Collector Current	I_C	50		mA
	Collector Power Dissipation (1 Circuit)	P_C	150	100	mW
	Collector Power Dissipation Derating (1 Circuit Ta \geq 25°C)	$\Delta P_C / ^\circ C$	-1.5	-1.0	mW / °C
	Junction Temperature	T_j	125		°C
Storage Temperature Range		T_{stg}	-55~150		°C
Operating Temperature Range		T_{opr}	-55~100		°C
Lead Soldering Temperature		T_{sol}	260 (10s)		°C
Total Package Power Dissipation		R_T	250	150	mW
Total Package Power Dissipation Derating (Ta \geq 25°C)		$\Delta P_T / ^\circ C$	-2.5	-1.5	mW / °C
Isolation Voltage		BV_S	2500 (AC, 1min., R.H. \leq 60%) (Note 1)		Vrms

(Note 1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V_{CC}	—	5	24	V
Forward Current	I_F	—	16	20	mA
Collector Current	I_C	—	1	10	mA
Operating Temperature	T_{opr}	-25	—	85	°C

961001EBC2'

- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to foreign exchange and foreign trade control laws.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
Capacitance Collector to Emitter	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F(\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V
		$I_C = 0.2\text{mA}, I_F = 1\text{mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

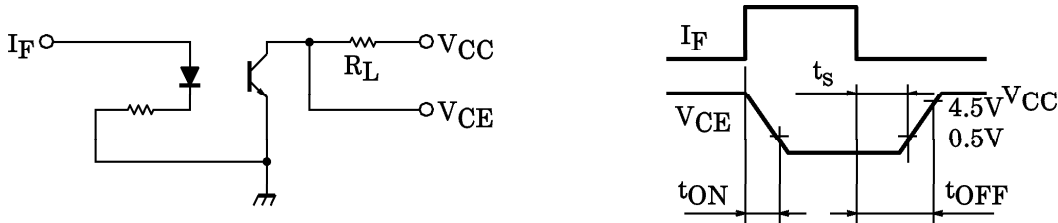
ISOLATION CHARACTERISTICS (Ta = 25°C)

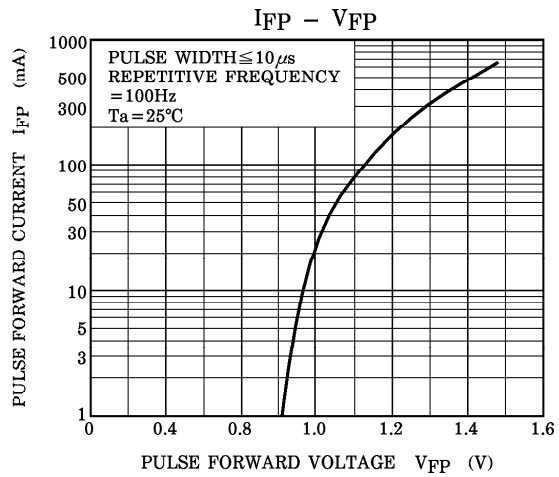
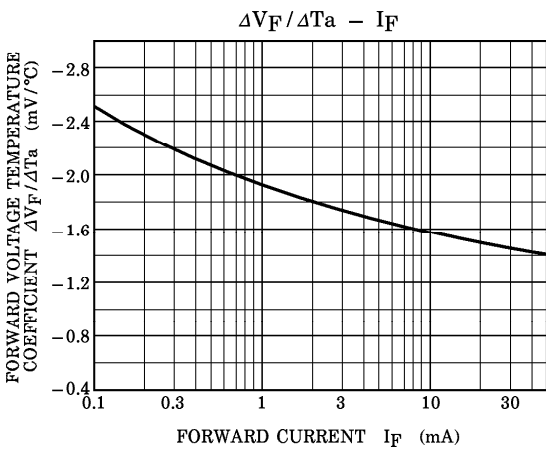
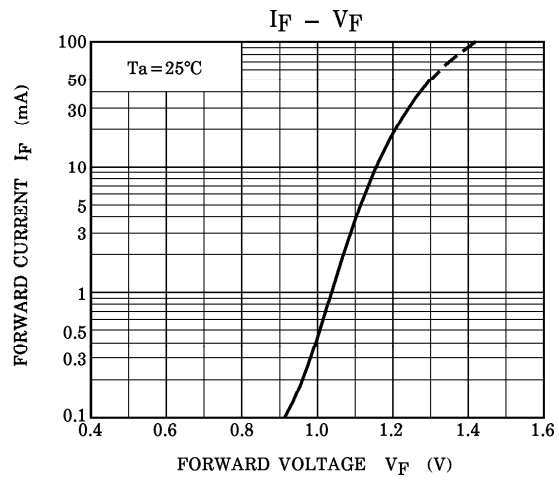
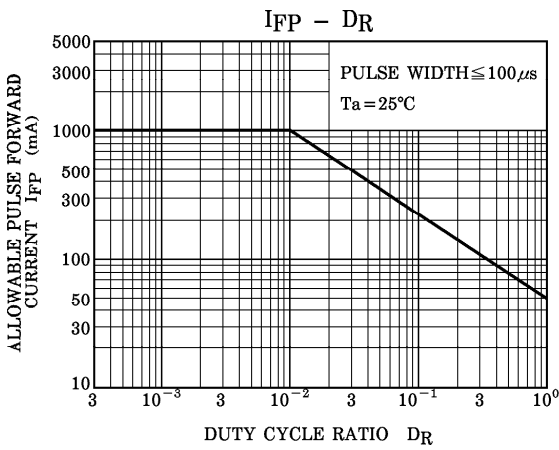
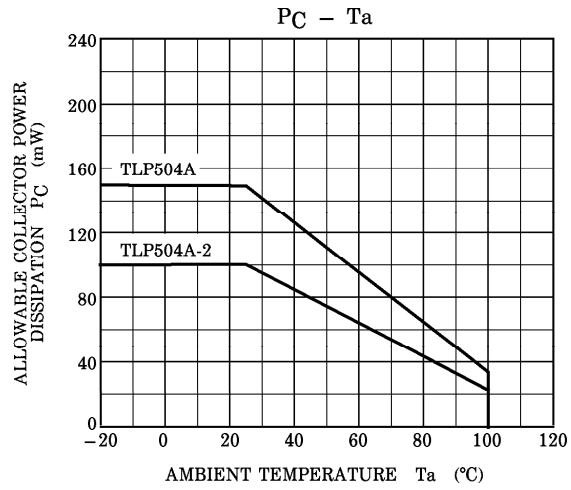
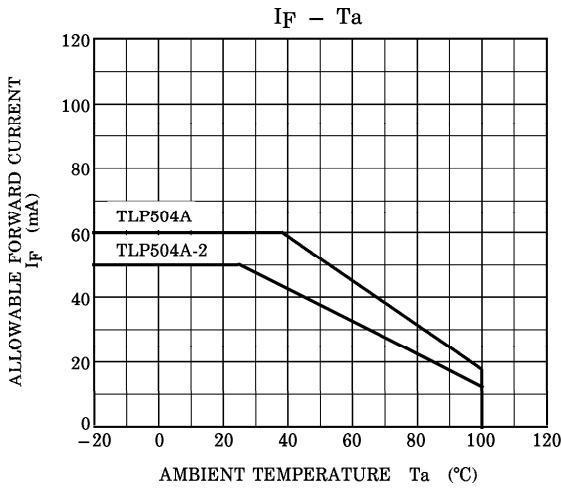
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}$	5×10^{10}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	2500	—	—	V_{rms}
		AC, 1 second, in oil	—	5000	—	
		DC, 1 minute, in oil	—	5000	—	Vdc

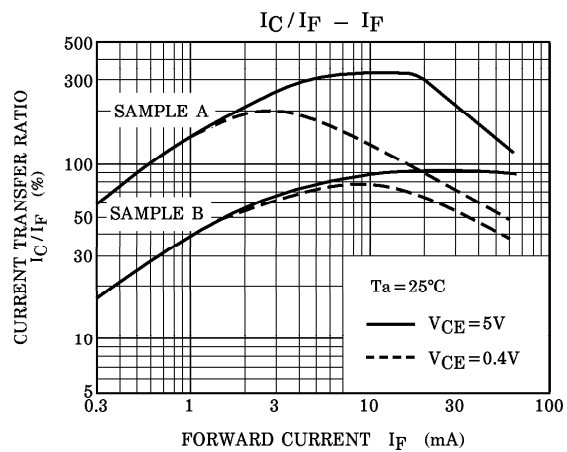
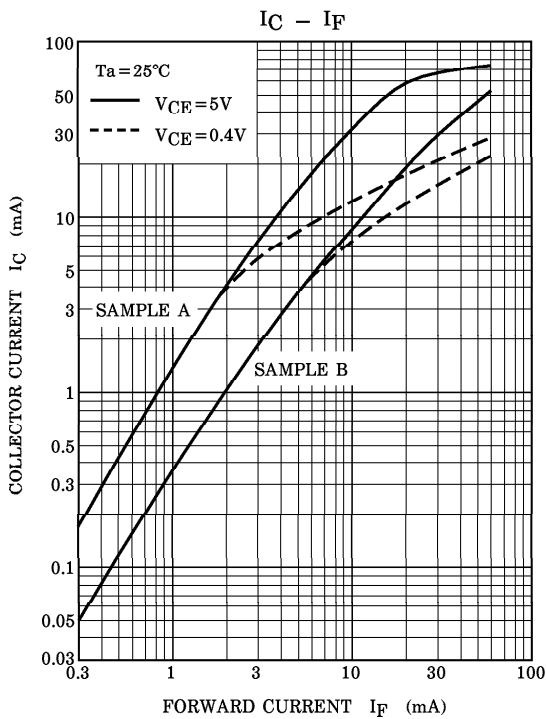
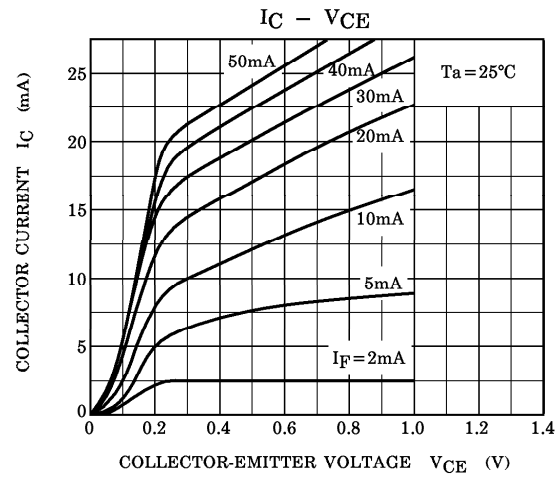
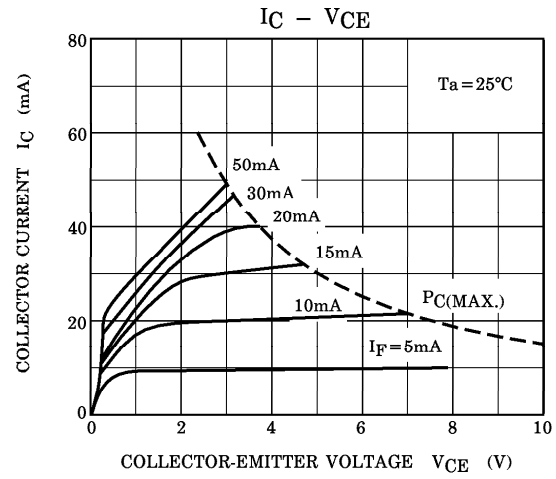
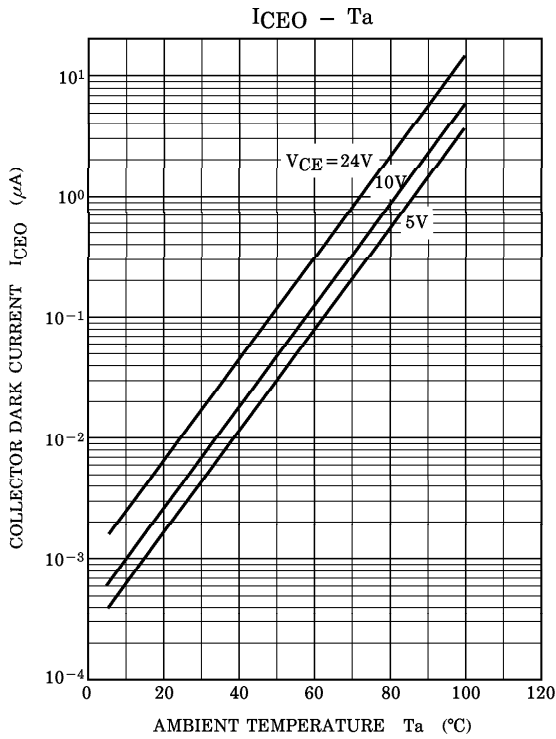
SWITCHING CHARACTERISTICS (Ta = 25°C)

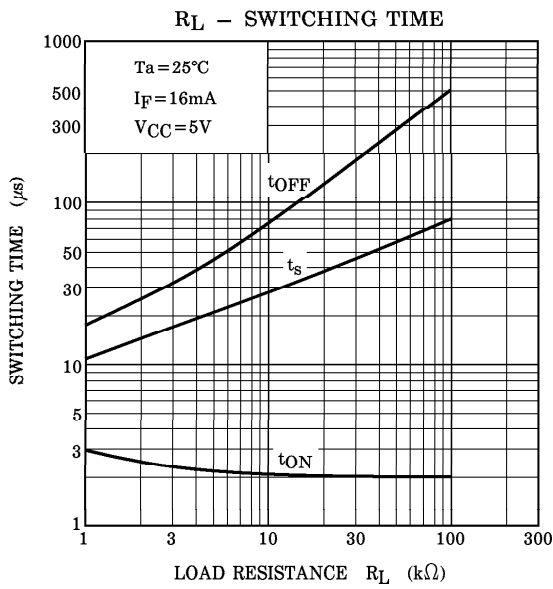
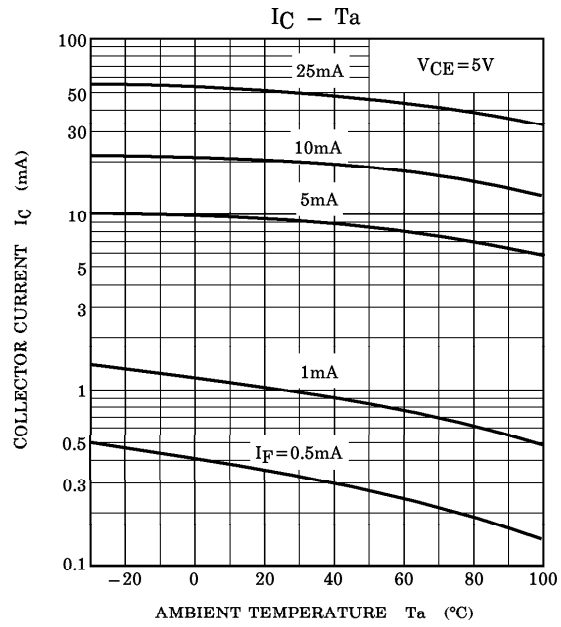
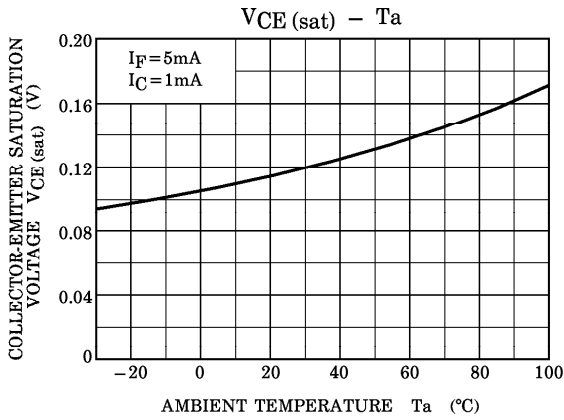
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t_r	$V_{CC} = 10V, I_C = 2mA$ $R_L = 100\Omega$	—	2	—	μs
Fall Time	t_f		—	3	—	
Turn-on Time	t_{on}		—	3	—	
Turn-off Time	t_{off}		—	3	—	
Turn-on Time	t_{ON}	$R_L = 1.9k\Omega$ (Fig.1) $V_{CC} = 5V, I_F = 16mA$	—	2	—	μs
Storage Time	t_s		—	15	—	
Turn-off Time	t_{OFF}		—	25	—	

Fig.1 Switching Time Test Circuit









单击下面可查看定价，库存，交付和生命周期等信息

[>>Toshiba\(东芝\)](#)